

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|--|---|------------------|
| 1 | 114 | @ad<=20001107 and 'bottom gate TFT' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/18 08:50 |
| - | 36 | @ad<=20001107 and 'thin film transistor' and 'selective' near 'doping' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/17 15:55 |
| - | 2 | @ad<=20001107 and 'thin film transistor' and 'cleaning' near 'native oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/16 14:53 |
| - | 1 | @ad<=20001107 and 'TFT' and 'cleaning' near 'native oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/16 14:53 |
| - | 18 | @ad<=20001107 and 'TFT' and 'remove' near 'native oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/17 16:10 |
| - | 7 | @ad<=20001107 and 'TFT' and 'removal' near 'native oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/16 15:06 |
| - | 590 | @ad<=20001107 and "thin film transistor" and "ohmic contact layer" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/16 15:26 |
| - | 60 | @ad<=20001107 and "thin film transistor" and "remove" near 'oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/17 08:43 |
| - | 1 | "3859716".PN. | USPAT | 2002/07/16 17:05 |
| - | 1 | "4757026".PN. | USPAT | 2002/07/16 17:05 |
| - | 1 | "4876213".PN. | USPAT | 2002/07/16 17:05 |
| - | 1 | "5182620".PN. | USPAT | 2002/07/16 17:06 |
| - | 1 | "5266823".PN. | USPAT | 2002/07/16 17:06 |
| - | 1 | "5323042".PN. | USPAT | 2002/07/16 17:06 |
| - | 1 | "5998841".PN. | USPAT | 2002/07/16 17:06 |
| - | 1 | "5962872".PN. | USPAT | 2002/07/16 17:06 |
| - | 1 | "5939731".PN. | USPAT | 2002/07/16 17:07 |
| - | 1 | "5804471".PN. | USPAT | 2002/07/16 17:08 |
| - | 1 | "5856689".PN. | USPAT | 2002/07/16 17:08 |
| - | 1 | "5804471".PN. | USPAT | 2002/07/16 17:08 |
| - | 3055 | ((438/149) or (438/158) or (438/315) or (438/334)).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/17 15:39 |
| - | 6 | ((((438/149) or (438/158) or (438/315) or (438/334)).CCLS.) and @ad<=20001107 and "thin film transistor" and "remove" near 'oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/17 15:50 |
| - | 608 | ((((438/149) or (438/158) or (438/315) or (438/334)).CCLS.) and @ad<=20001107 and "thin film transistor" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/17 08:46 |

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|---|-------|--|---|------------------|
| - | 5525 | ((438/149) or (438/158-159) or (438/315) or (438/334) or (438/163) or (438/166) or (257/69) or (257/72) or (257/59)).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/17 15:43 |
| - | 16 | ((438/149) or (438/158-159) or (438/315) or (438/334) or (438/163) or (438/166) or (257/69) or (257/72) or (257/59)).CCLS.) and @ad<=20001107 and "thin film transistor" and "remove" near 'oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/17 15:51 |
| - | 1 | @ad<=20001107 and 'thin film transistor' and 'burried gate' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/17 15:56 |
| - | 30430 | @ad<=20001107 and 'thin film transistor' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/17 15:59 |
| - | 779 | (@ad<=20001107 and 'thin film transistor') and short same channel | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/17 16:01 |
| - | 719 | (@ad<=20001107 and 'thin film transistor') and short same channel and gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/17 16:02 |
| - | 18 | @ad<=20001107 and 'TFT' and 'remove' near 'native oxide' | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/18 08:50 |
| - | 1 | "5641974".PN. | USPAT | 2002/12/17 16:13 |
| - | 1 | "5780871".PN. | USPAT | 2002/12/17 16:13 |
| - | 1 | "5837619".PN. | USPAT | 2002/12/17 16:14 |
| - | 1 | "5882165".PN. | USPAT | 2002/12/17 16:14 |
| - | 1 | "5917571".PN. | USPAT | 2002/12/17 16:14 |
| - | 1 | "6177302".PN. | USPAT | 2002/12/17 16:14 |
| - | 4767 | ((257/59) or (257/61) or (257/72) or (257/347) or (349/42-43)).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/17 16:18 |

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| - | 1 | "4876213".PN. | USPAT | 2002/07/16 17:05 |
| - | 1 | "5182620".PN. | USPAT | 2002/07/16 17:06 |
| - | 1 | "5266823".PN. | USPAT | 2002/07/16 17:06 |
| - | 1 | "5323042".PN. | USPAT | 2002/07/16 17:06 |
| - | 1 | "5998841".PN. | USPAT | 2002/07/16 17:06 |
| - | 1 | "5962872".PN. | USPAT | 2002/07/16 17:06 |
| - | 1 | "5939731".PN. | USPAT | 2002/07/16 17:07 |
| - | 1 | "5804471".PN. | USPAT | 2002/07/16 17:07 |
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| - | 1 | "5837619".PN. | USPAT | 2002/12/17 16:14 |
| - | 1 | "5882165".PN. | USPAT | 2002/12/17 16:14 |
| - | 1 | "5917571".PN. | USPAT | 2002/12/17 16:14 |
| - | 1 | "6177302".PN. | USPAT | 2002/12/17 16:14 |
| - | 4767 | ((257/59) or (257/61) or (257/72) or (257/347) or (349/42-43)).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/12/17 16:18 |